

1. General description

Planar passivated Silicon Controlled Rectifier in a TO-247 plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance. This product is qualified to AEC-Q101 standard for use in automotive applications.



AEC - Q101 Qualified



Lead-Free

2. Features and benefits

- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- High voltage capacity
- Very high current surge capability
- AEC-Q101 compliant

3. Applications

- Automotive battery charging (on-board and off-board)
- Solid State Relay (SSR)
- Uninterruptible Power Supply (UPS)
- Inrush protection and soft-start
- AC and DC motor controls
- Heating controls
- AC Power rectification
- Renewable energy inverters
- Industrial welding systems

4. Quick reference data

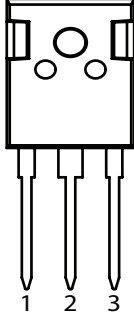
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Absolute maximum rating						
V_{DRM}	repetitive peak off-state voltage		-	-	1200	V
V_{RRM}	repetitive peak reverse voltage		-	-	1200	V
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{J(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	650	A
		half sine wave; $T_{J(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	-	715	A
T_J	junction temperature		-	-	150	$^{\circ}\text{C}$
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 131\text{ }^{\circ}\text{C}$	-	-	50	A

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 131\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		-	-	79	A
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^{\circ}\text{C}$; Fig. 7 ; Fig. 8		-	-	50	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 804\text{ V}$; $T_J = 125\text{ }^{\circ}\text{C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform		1500	-	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT155W-1200T-A	TO-247	BT155W-1200T-AQ	Tube	30	TO-247N	20-Jul-2016

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT155W-1200T-A	BT155W-1200T-A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1200	V
V_{RRM}	repetitive peak reverse voltage		-	1200	V
$I_{\text{T(AV)}}$	average on-state current	half sine wave; $T_{\text{mb}} \leq 131\text{ }^{\circ}\text{C}$	-	50	A
$I_{\text{T(RMS)}}$	RMS on-state current	half sine wave; $T_{\text{mb}} \leq 131\text{ }^{\circ}\text{C}$; Fig 1 ; Fig 2 ; Fig 3	-	79	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{\text{J(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 10\text{ ms}$; Fig 4 ; Fig 5	-	650	A
		half sine wave; $T_{\text{J(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 8.3\text{ ms}$	-	715	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse	-	2113	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 100\text{mA}$	-	150	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	8	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_{J}	junction temperature		-	150	$^{\circ}\text{C}$

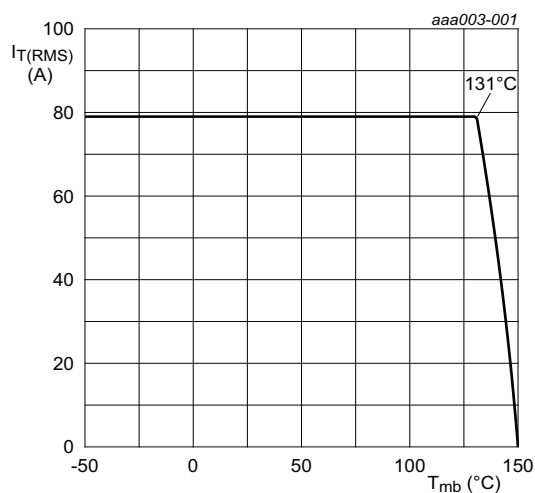
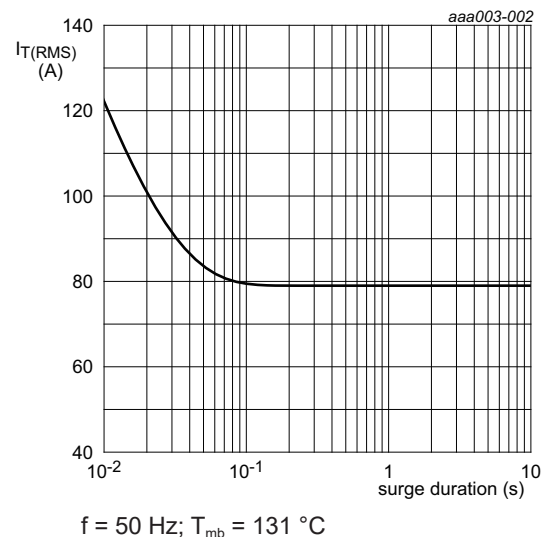


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{\text{mb}} = 131\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

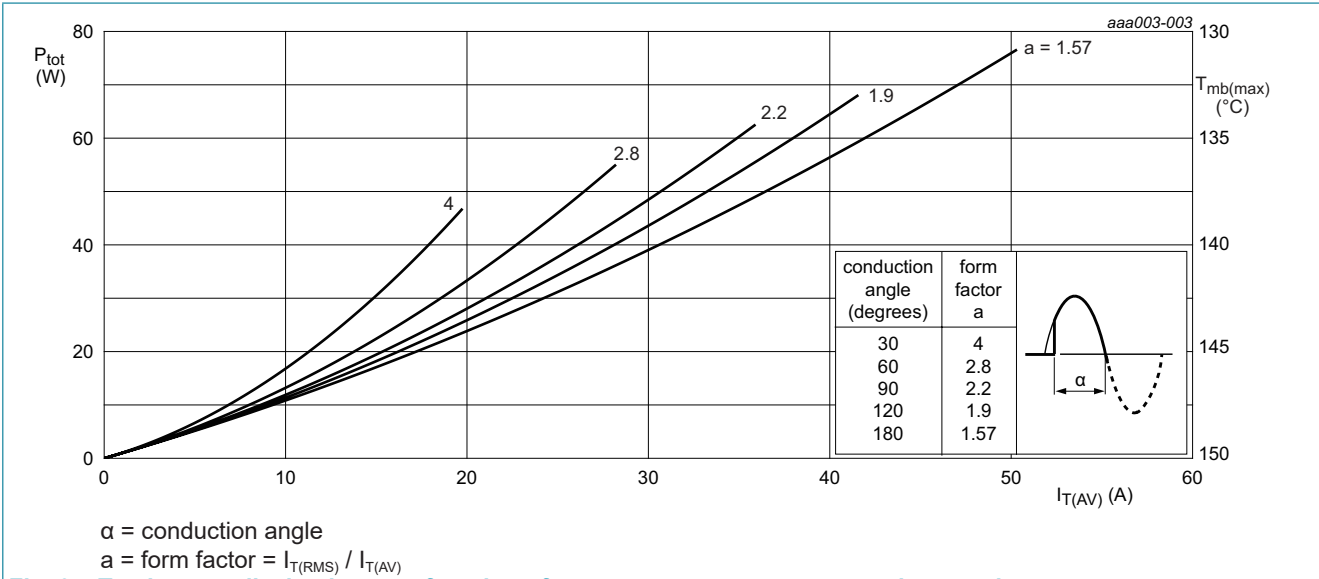


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

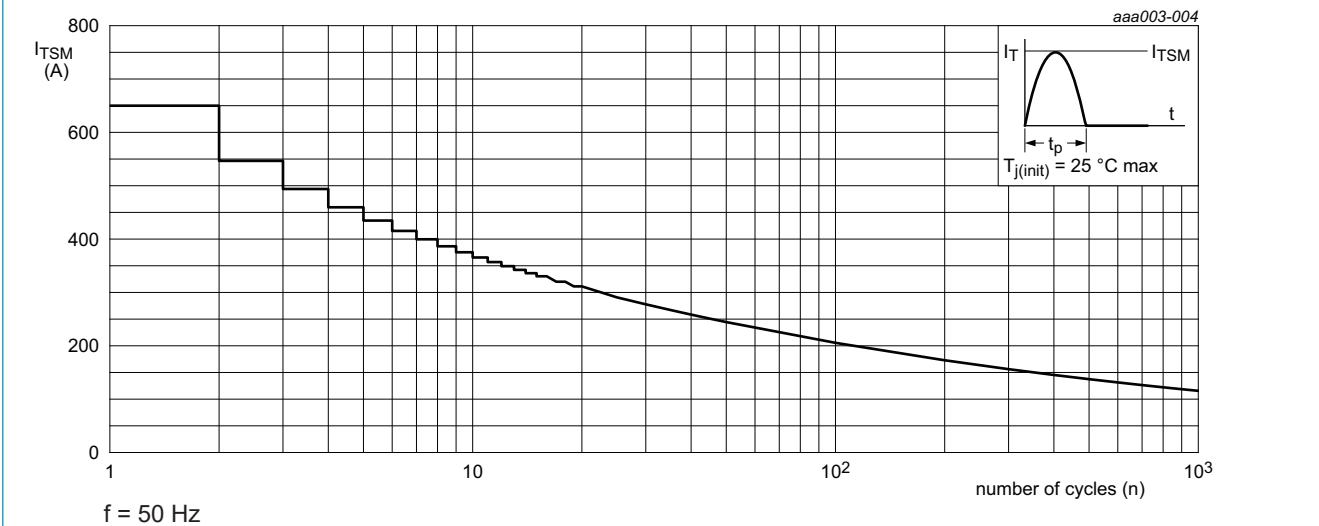


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

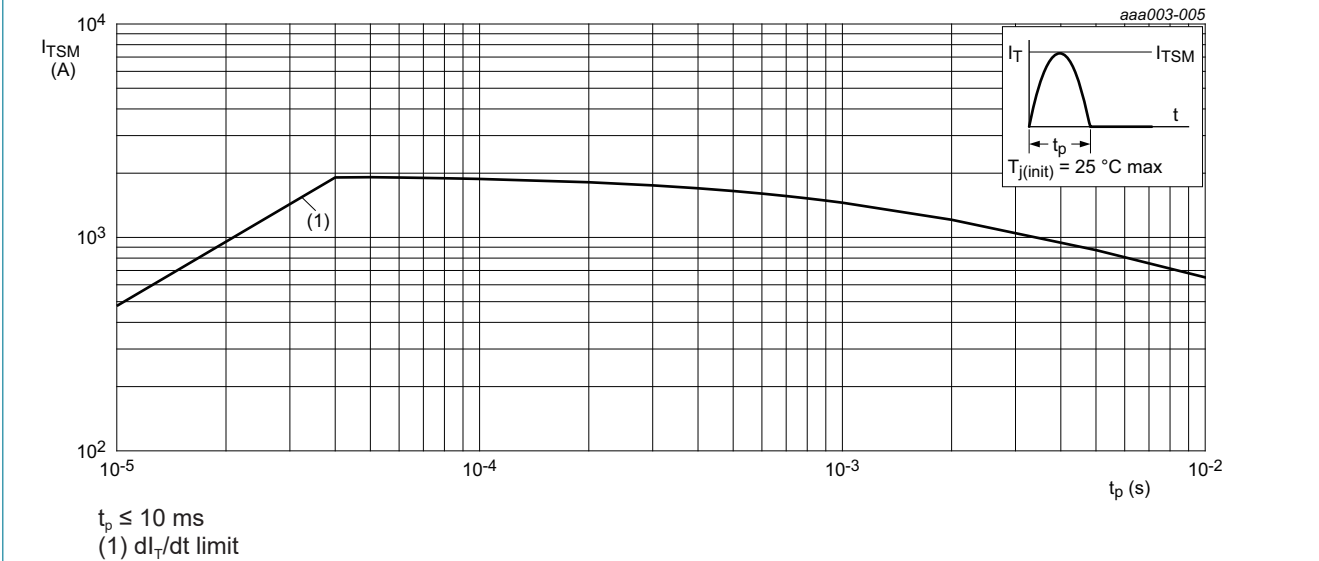
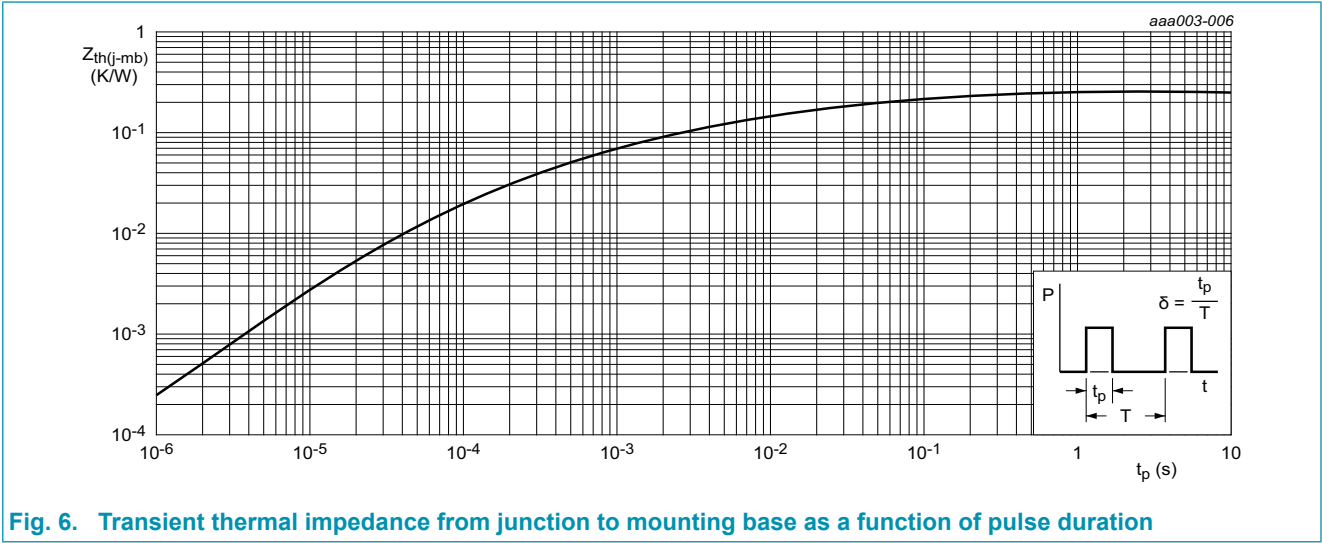


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig 6		-	-	0.25	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	50	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7 ; Fig. 8	-	-	50	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	300	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10	-	-	200	mA
V_T	on-state voltage	$I_T = 50\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11	-	-	1.3	V
		$I_T = 90\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11	-	-	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 12	-	0.7	1	V
		$V_D = 800\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$; Fig. 12	0.25	0.4	-	V
I_D	off-state current	$V_D = 1200\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$	-	-	3	mA
I_R	reverse current	$V_D = 1200\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$	-	-	3	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 804\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform	1500	-	-	V/ μs
		$V_{DM} = 804\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform	1000	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$; $V_D = 800\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$; $T_J = 25\text{ }^\circ\text{C}$	-	2	-	μs
t_q	commutated turn-off time	$V_{DM} = 804\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $I_{TM} = 20\text{ A}$; $V_R = 25\text{ V}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $R_{GK(ext)} = 100\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM})	-	150	-	μs

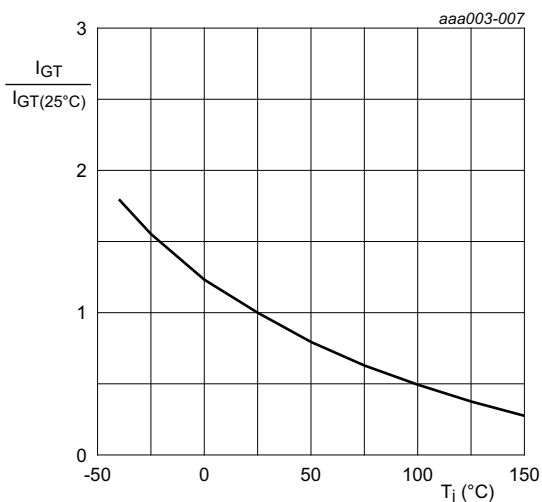


Fig. 7. Normalized gate trigger current as a function of junction temperature

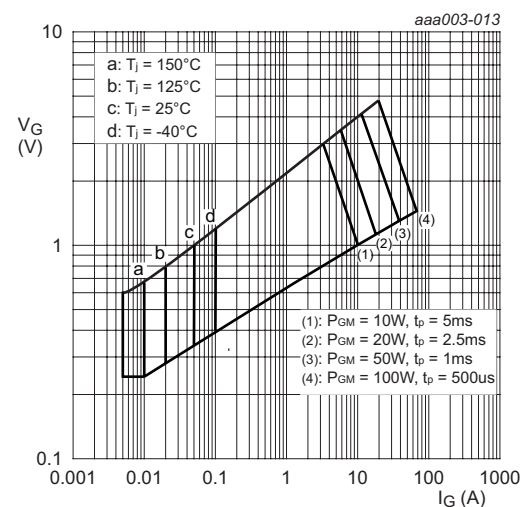


Fig. 8. Gate voltage as a function of gate current

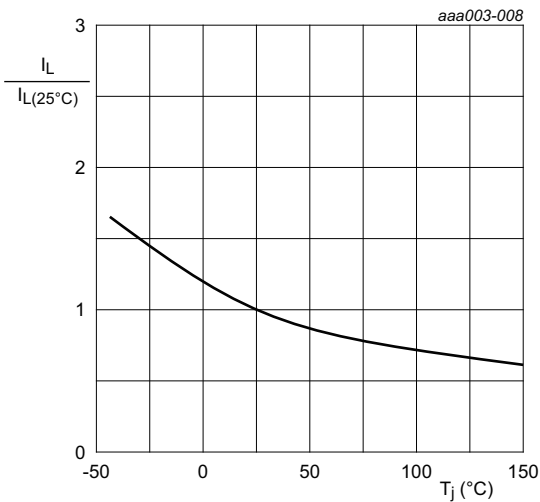


Fig. 9. Normalized latching current as a function of junction temperature

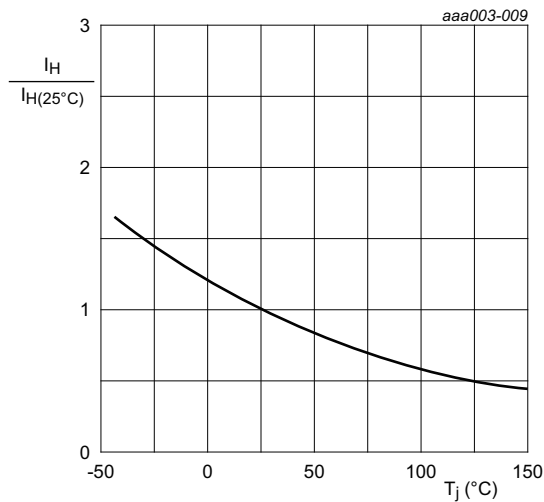
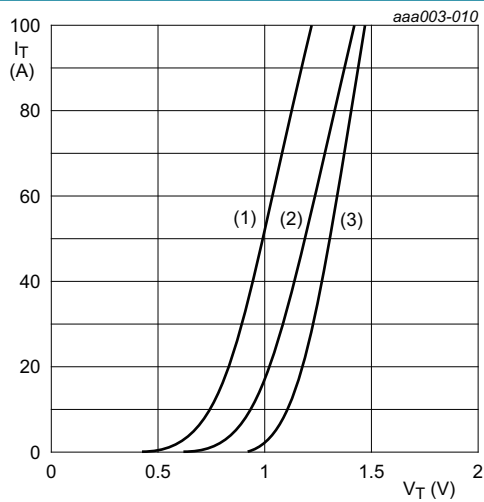


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 0.975 \text{ V}$; $R_s = 0.0044 \text{ } \Omega$
(1) $T_j = 150^\circ\text{C}$; typical values
(2) $T_j = 150^\circ\text{C}$; maximum values
(3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 11. On-state current as a function of on-state voltage

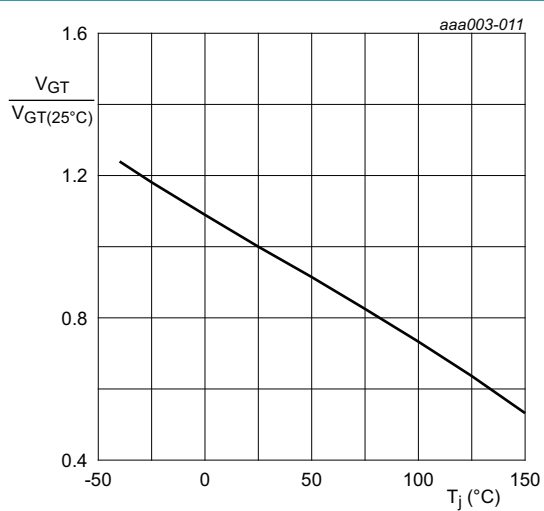
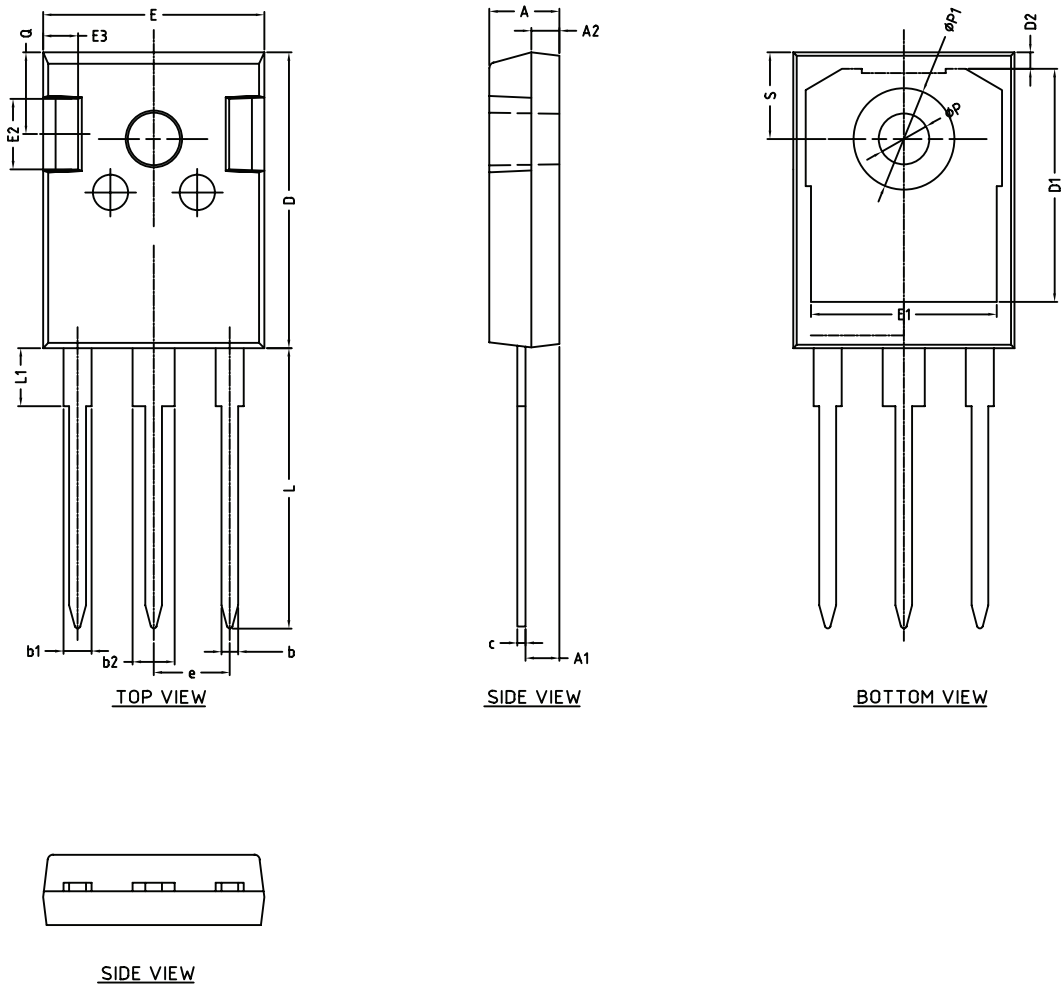


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 SOT429N



UNIT	A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S
mm	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	5.45	20.10	4.75	3.70	7.40	6.00	6.25
	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40		19.80	-	3.50	-	5.60	6.05

OUTLINE VERSION	REFERENCES				PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT429N		TO-247				

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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